

### **Description**

The AR1511D3 is a 15V bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The AR1511D3 has a low capacitance with a typical value at 1pF, and complies with the IEC 61000-4-2 (ESD) with ±25kV air and ±20kV contact discharge. It is assembled into a lead-free SOD-323 package. The small size, low capacitance and high ESD surge protection make AR1511D3 an ideal choice to protect cell phone, wireless systems, and communication equipment.

### **Features**

300W peak pulse power (8/20µs)

Ultra low capacitance: 1pF typical

Ultra low leakage: nA leel

Operating voltage: 15V

Low clamping voltage

· Protects one power line or data line

• Complies with following standards:

IEC 61000-4-2 (ESD) immunity test
 Air discharge: ±25kV

Contact discharge: ±20kV

- IEC61000-4-5 (Lightning) 8A (8/20µs)

RoHS Compliant

### **Mechanical Characteristics**

Package: SOD-323Lead Finish: Matte Tin

Case Material: "Green" Molding Compound.Terminal Connections: See Diagram Below

Marking Information: See Below

### **Applications**

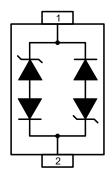
- USB Ports
- Smart Phones
- Wireless Systems
- Ethernet 10/100/1000 Base T

### **Marking Information**



#### **Ordering Information**

### **Dimensions and Pin Configuration**



Circuit and Pin Schematic

Part Number	Packaging	Reel Size	
AR1511D3	3000/Tape & Reel	7 inch	



## Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise specified)

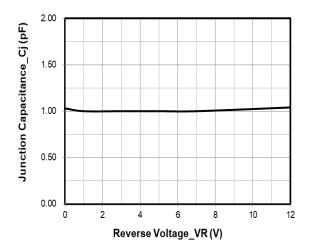
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	240	W
Peak Pulse Current (8/20µs)	IPP	8	Α
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	VESD	±25 ±20	kV
Operating Temperature Range	TJ	-40 to +85	°C
Storage Temperature Range	Tstg	−55 to +150	°C

# Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise specified)

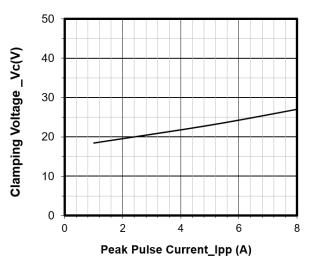
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			15	V	
Breakdown Voltage	VBR	16.7			V	IT = 1mA
Reverse Leakage Current	I <sub>R</sub>			0.2	μA	VRWM = 15V
Clamping Voltage	Vc			21	V	IPP = 1A (8 x 20μs pulse)
Clamping Voltage	Vc			30	V	IPP = 8A (8 x 20μs pulse)
Junction Capacitance	CJ		1		pF	VR = 0V, f = 1MHz



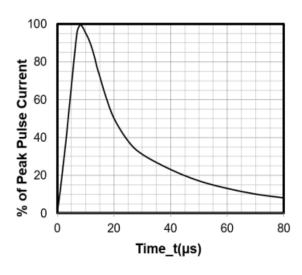
### Typical Performance Characteristics (TA=25°C unless otherwise Specified)



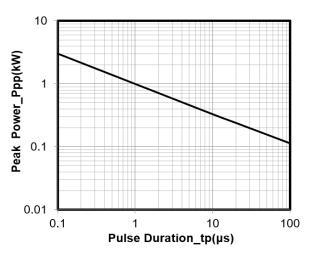
Junction Capacitance vs. Reverse Voltage



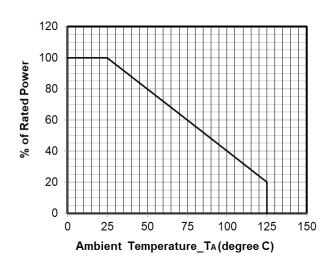
Clamping Voltage vs. Peak Pulse Current



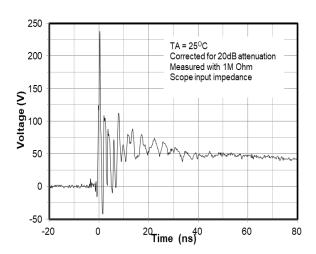
8 X 20µs Pulse Waveform



Peak Pulse Power vs. Pulse Time



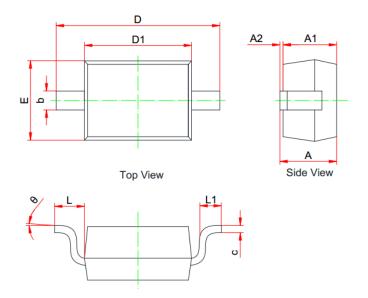
**Power Derating Curve** 



ESD Clamping Voltage 8 kV Contact per IEC61000-4-2



## **SOD-323 Package Outline Drawing**



	MILLIMETERS				
	MIN	NOM	MAX		
Α	0.800		1.100		
A1	0.800		0.900		
A2	0.000		0.100		
b	0.250		0.400		
С	0.080		0.177		
D1	1.600	1.700	1.800		
D	2.300		2.800		
E	1.150		1.400		
L	0.475REF				
L1	0.100		0.500		
Θ	0°		8°		

## **Suggested Land Pattern**



Unit: mm

### **Contact Information**

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